

**IN THE SPECIFICATION**

Please amend the paragraph beginning at page 13, line 4 and ending at page 13, line 13 [¶ 0074] as follows:

--Inter-layer reaction layers 94, 96 and 98, which include at least  $Al_xSi_x$  made of aluminum and silicon, wherein x is an integer, and can be the same or a different value for Al and Si, respectively, or inter-metallic compound, are at least formed on the portion of the gate pad 24, the drain electrode 66 and the data pad 68, which are exposed through contact holes 74, 76 and 78. Here, the inter-layer reaction layers 94, 96 and 98 have the function improving contact prosperities between the gate pad 24 and the upper layer 602 of the drain electrode 66 and the data pad 68, which is made of aluminum-based material, and a pixel wire 82, 86 and 88 of IZO, which be formed later. It is preferable that the intermetallic compound includes transition metal such as chromium, molybdenum, molybdenum alloy etc.—

Please amend the paragraph beginning at page 22, line 9, and ending at page 22, line 13 [¶ 0105] as follows:

--Inter-layer reaction layers 91, 92, 93 and 94, which include at least  $Al_xSi_x$  made of aluminum and silicon, wherein x is an integer, and can be the same or a different value for Al and Si, respectively, or inter-metallic compound, are at least formed on the portion of the drain electrode 66, the gate pad 24, the data pad 68 and the conductor pattern 64, which are exposed through contact holes 71, 72, 73 and 74.--